



GSX25N65E

MOSFET

Metal Oxide Semiconductor Field Effect Transistor

Super Junction MOSFET

650V Super Junction Power Transistor

GSX25N65E

Data Sheet

Ver 1.0

2018-3-20

650V 25A Power MOSFET

Description

Group Semiconductor(GS) has series Multi-EPI Super-Junction power MOSFET platforms for voltage up 500V to 1000 volts, both with design service and manufacturing capability, including cell, termination design and simulation.

The GS 650V 25A power MOSFET is a Low voltage N channel Multi-EPI Super-Junction power MOSFET sample with advanced technology to have better characteristics, such as fast switching time, low Ciss and Crss, low on resistance and excellent avalanche characteristics, making it especially suitable for applications which require superior power density and outstanding efficiency.

Features

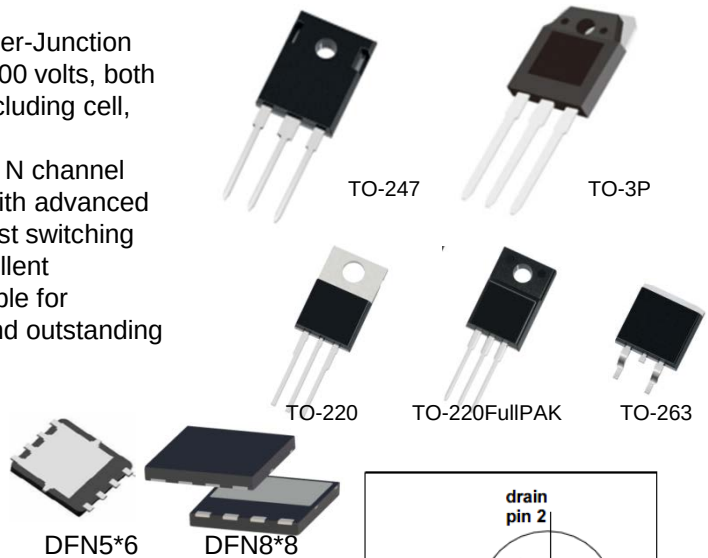
$R_{DS(ON)} = 0.14\Omega$ @ $V_{GS} = 10V$

$V_{DS} = 650V$

I_D (@ $V_{GS} = 10V$) = 12A

PKG

GSA25N65E	GSP25N65E	GSB25N65E		
TO-220Fullpak	TO-220	TO-263		
GSW25N65E	GSJ25N65E	GSN25N65E	GSM25N65E	
TO-247	TO-3P	DFN5*6	DFN8*8	



Absolute Maximum Ratings (TC = 25° C, unless otherwise specified)

Symbol	Parameter	GSP25N65E	GSA25N65E	Unit
V_{DS}	Drain-Source Voltage	650		V
I_D	Drain Current -Continuous (TC = 25°C) -Continuous (TC = 100°C)	25* 15*		A
I_{DM}	Drain Current - Pulsed (Note 1)	53		A
V_{GS}	Gate-Source voltage	±30		V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	500		mJ
I_{AR}	Avalanche Current (Note 1)	4		A
E_{AR}	Repetitive Avalanche Energy (Note 1)	1.2		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	15		V/ns
dV_{DS}/dt	Drain Source voltage slope (Vds=480V)	50		V/ns
P_D	Power Dissipation (TC = 25°C)	151	35	W
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150		°C
T_L	Max. Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300		°C

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■ Electrical Characteristics (T_J=25° C unless otherwise specified)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA, T _J = 25°C	650	--	--	V
		V _{GS} = 0V, I _D = 250μA, T _J = 150°C	--	700	--	V
ΔBV _{DSS} /ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250μA, Referenced to 25°C	--	0.6	--	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 650V, V _{GS} = 0V -T _j =25 °C -T _J = 150°C	--	-- 10	1 -	μA μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30V, V _{DS} = 0V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30V, V _{DS} = 0V	--	--	-100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	2	--	4	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10V, I _D = 12A	--	0.12	0.14	Ω
g _{FS}	Forward Transconductance	V _{DS} = 40V, I _D = 12A	--	16	--	S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz	--	1650	-	pF
C _{oss}	Output Capacitance		--	90	-	pF
C _{rss}	Reverse Transfer Capacitance		--	9	--	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 520Ω (Note 4)	--	28	--	ns
t _r	Turn-On Rise Time		--	19	--	ns
t _{d(off)}	Turn-Off Delay Time		--	140	--	ns
t _f	Turn-Off Fall Time		--	12	--	ns
Q _g	Total Gate Charge	V _{DS} = 520V, I _D = 12A	--	110	140	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10V (Note 4)	--	9	--	nC
Q _{gd}	Gate-Drain Charge		--	15	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	25	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	75	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0V, I _S = 12A	--	0.9	1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _S = 12A	--	500	--	ns
Q _{rr}	Reverse Recovery Charge	dI _F /dt =100A/μs	--	6	--	μC

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L=60mH, I_{AS}=3A, V_{DD}=150V, Starting T_J=25 °C
3. I_{SD}≤4.5A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25 °C
4. Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%
5. Essentially Independent of Operating Temperature Typical Characteristics

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■ Thermal Characteristics

Symbol	Parameter	GSA25N65E	GSP25N65E	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	1.2	1.2	$^{\circ}\text{C}/\text{W}$
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink Typ.	0.5	0.5	$^{\circ}\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62	62	$^{\circ}\text{C}/\text{W}$

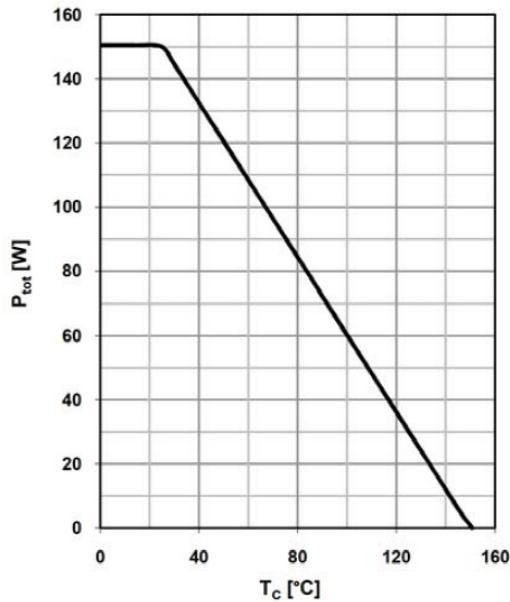
Symbol	Parameter	Value (TO220)	Unit
$R_{\theta JA}^{(6)}$	Maximum Junction-to-Ambient	82	$^{\circ}\text{C}/\text{W}$
$R_{\theta CS}^{(6)}$	Maximum Case-to-sink	0.6	$^{\circ}\text{C}/\text{W}$
$R_{\theta JC}^{(7),(8)}$	Maximum Junction-to-Case θ	4.1	$^{\circ}\text{C}/\text{W}$

1. The power dissipation PD is based on $T_J(\text{MAX})=150^{\circ}\text{C}$ in a TO251 package, using junction-to-case thermal resistance.
2. Repetitive rating, pulse width limited by junction temperature $T_J(\text{MAX})=150^{\circ}\text{C}$.
3. $L=1\text{mH}$, Starting $T_J=25^{\circ}\text{C}$.
4. $L=10\text{mH}$, starting $T_J=25^{\circ}\text{C}$.
5. $L=60\text{mH}$, starting $T_J=25^{\circ}\text{C}$.
6. The tests are performed with the device with $T_A=25^{\circ}\text{C}$.
7. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.
8. These curves are based on the junction-to-case thermal impedance, assuming a maximum junction temperature of $T_J(\text{MAX})=150^{\circ}\text{C}$.

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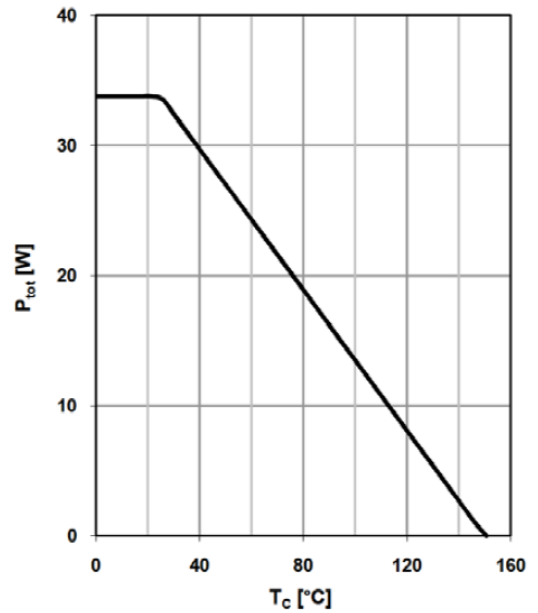
Typical Performance Characteristics

**Power dissipation
Non FullPAK**



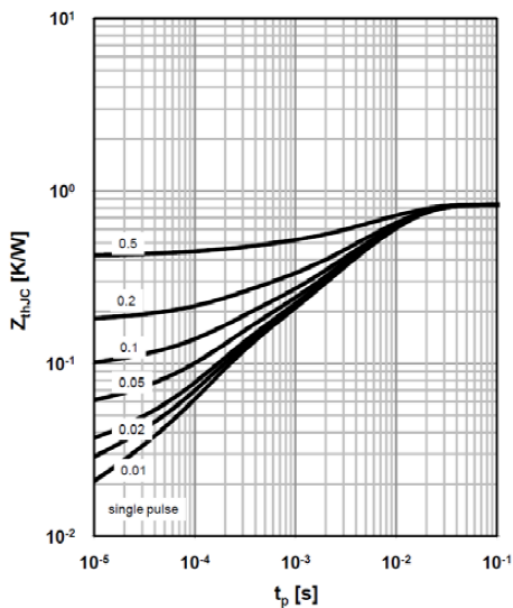
$$P_{tot} = f(T_c)$$

**Power dissipation
FullPAK**



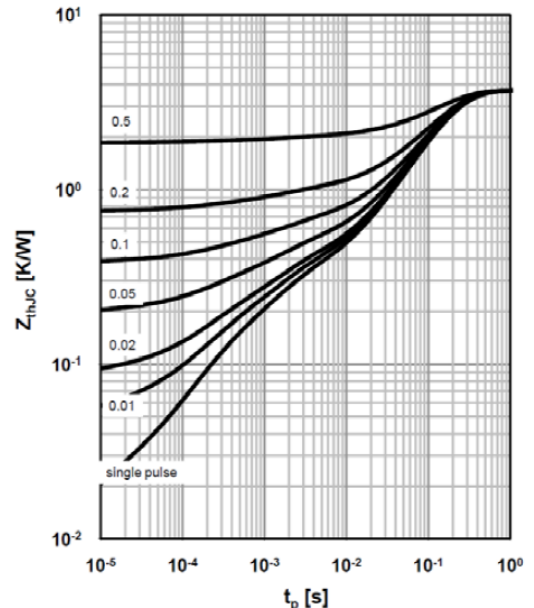
$$P_{tot} = f(T_c)$$

**Max. transient thermal impedance
Non FullPAK**



$$Z_{(thJC)} = f(t_p); \text{ parameter: } D = t_p / T$$

**Max. transient thermal impedance
FullPAK**

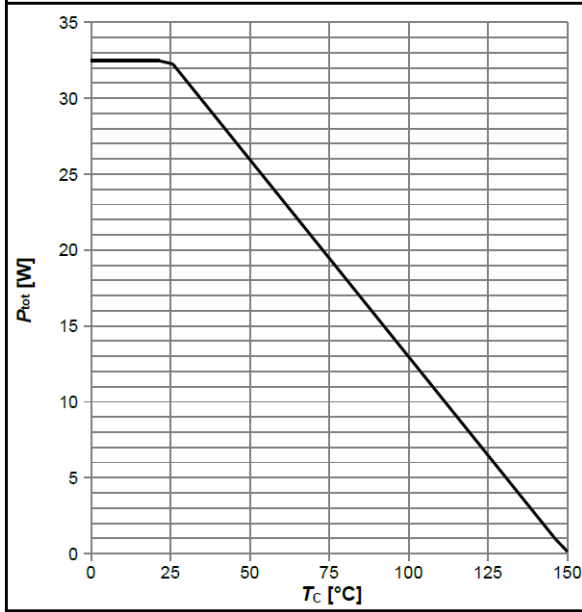


$$Z_{(thJC)} = f(t_p); \text{ parameter: } D = t_p / T$$

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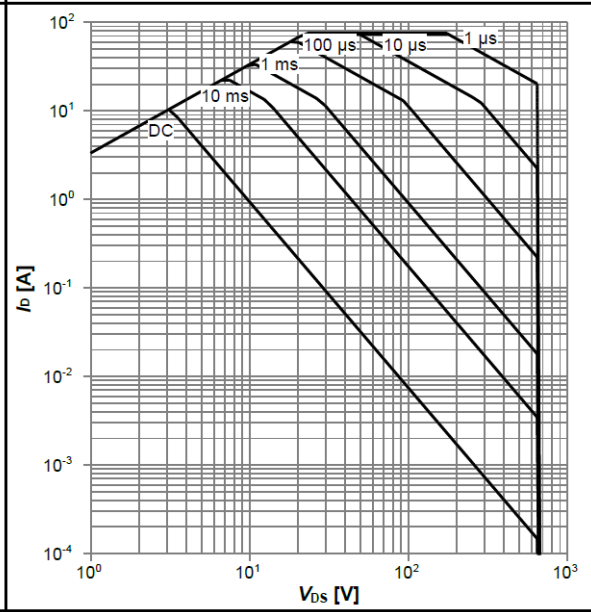
Typical Performance Characteristics

Diagram 1: Power dissipation



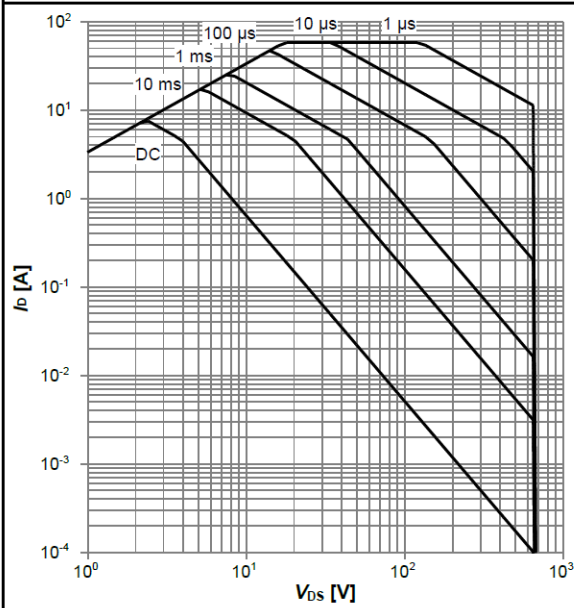
$$P_{tot} = f(T_c)$$

Diagram 2: Safe operating area



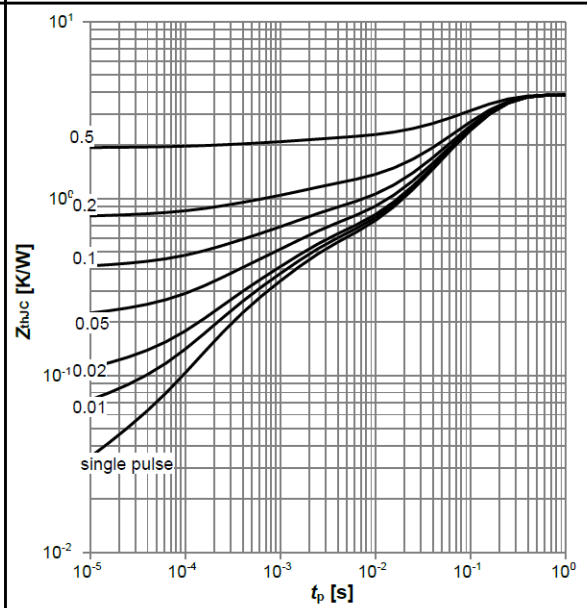
$$I_b = f(V_{DS}); T_c = 25 \text{ °C}; D = 0; \text{parameter: } t_p$$

Diagram 3: Safe operating area



$$I_b = f(V_{DS}); T_c = 80 \text{ °C}; D = 0; \text{parameter: } t_p$$

Diagram 4: Max. transient thermal impedance

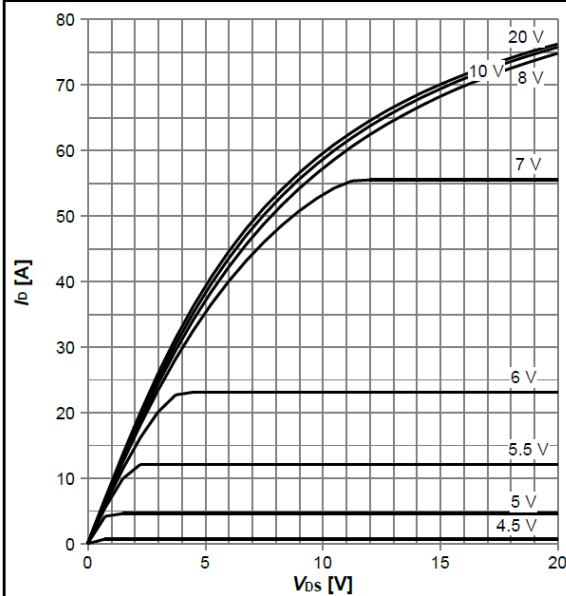


$$Z_{thJC} = f(t_p); \text{parameter: } D = t_p / T$$

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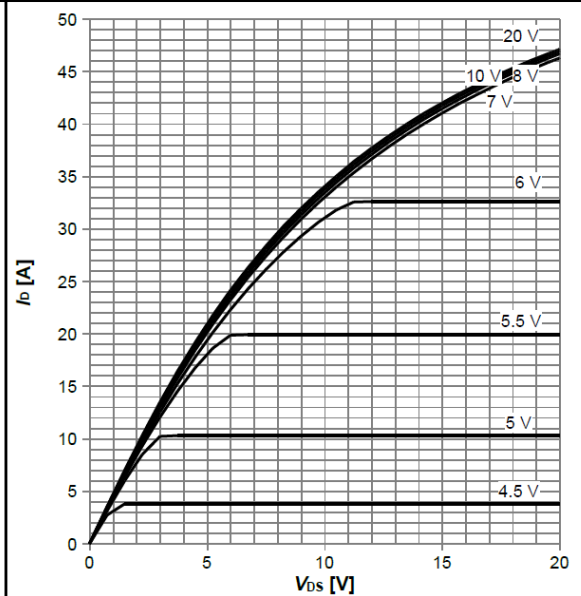
Typical Performance Characteristics

Diagram 5: Typ. output characteristics



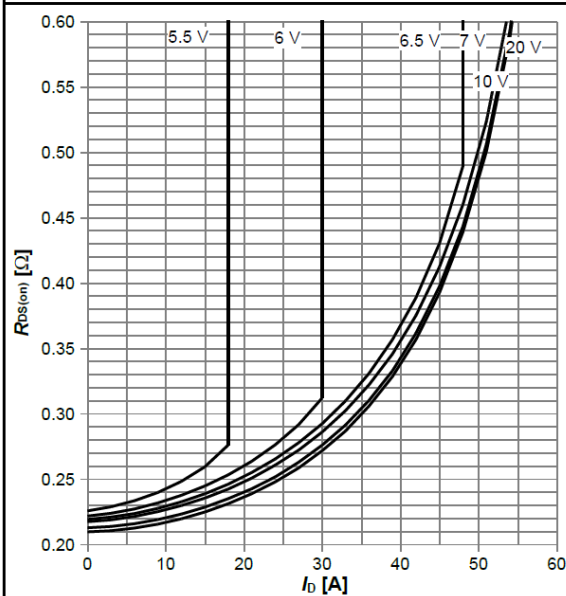
$I_D = f(V_{DS})$; $T_j = 25\text{ }^{\circ}\text{C}$; parameter: V_{GS}

Diagram 6: Typ. output characteristics



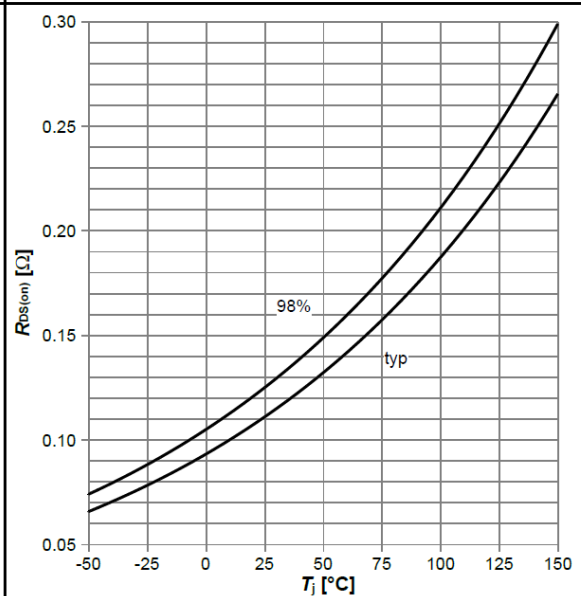
$I_D = f(V_{DS})$; $T_j = 125\text{ }^{\circ}\text{C}$; parameter: V_{GS}

Diagram 7: Typ. drain-source on-state resistance



$R_{DS(on)} = f(I_D)$; $T_j = 125\text{ }^{\circ}\text{C}$; parameter: V_{GS}

Diagram 8: Drain-source on-state resistance

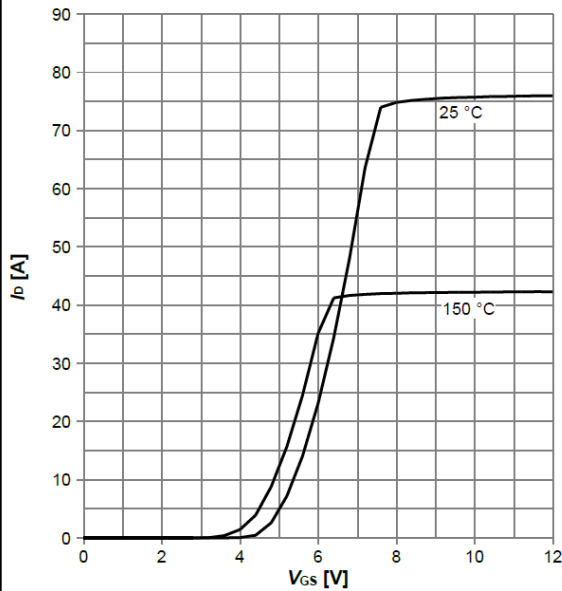


$R_{DS(on)} = f(T_j)$; $I_D = 8.9\text{ A}$; $V_{GS} = 10\text{ V}$

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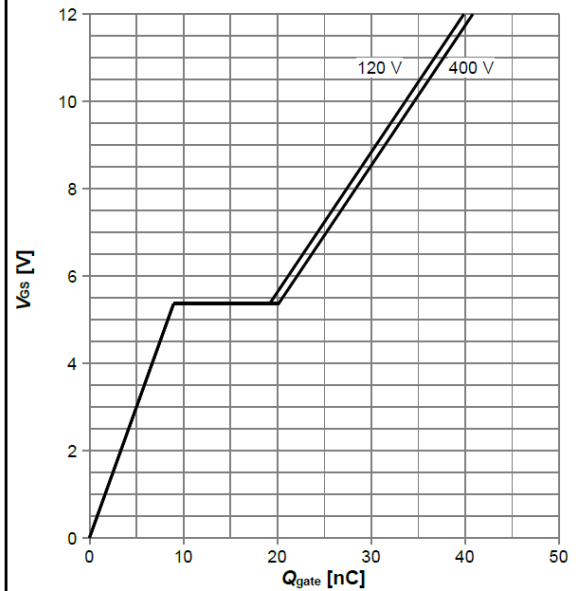
Typical Performance Characteristics

Diagram 9: Typ. transfer characteristics



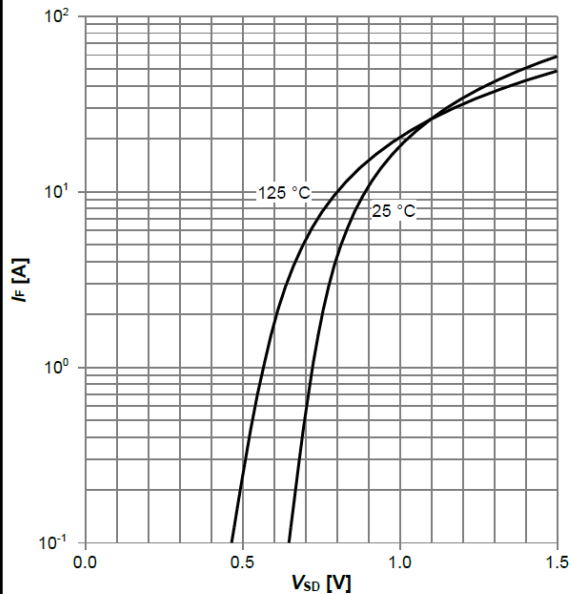
$I_D = f(V_{GS})$; $V_{DS} = 20\text{ V}$; parameter: T_j

Diagram 10: Typ. gate charge



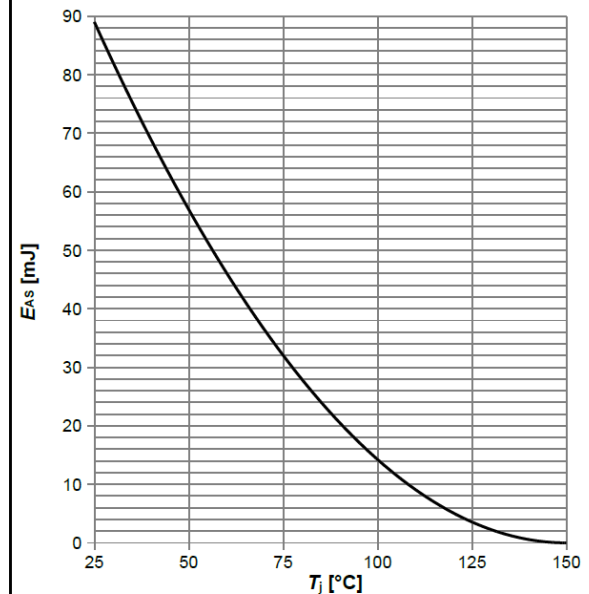
$V_{GS} = f(Q_{gate})$; $I_D = 8.9\text{ A}$ pulsed; parameter: V_{DD}

Diagram 11: Forward characteristics of reverse diode



$I_F = f(V_{SD})$; parameter: T_j

Diagram 12: Avalanche energy

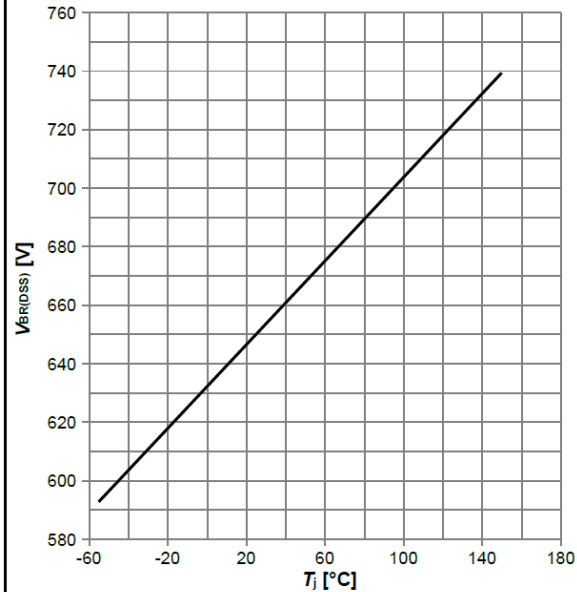


$E_{AS} = f(T_j)$; $I_D = 7.1\text{ A}$; $V_{DD} = 50\text{ V}$

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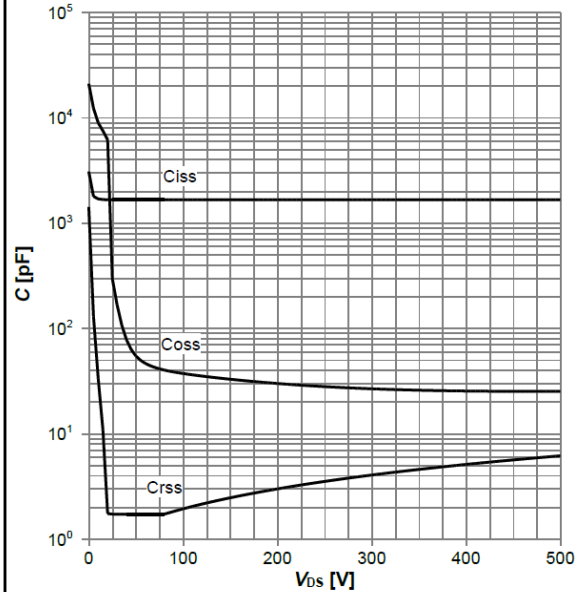
Typical Performance Characteristics

Diagram 13: Drain-source breakdown voltage



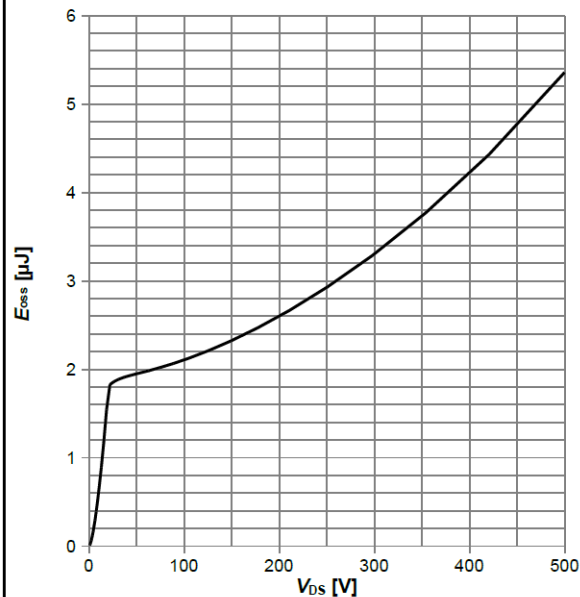
$$V_{BR(DSS)} = f(T_j); I_D = 1 \text{ mA}$$

Diagram 14: Typ. capacitances



$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 250 \text{ kHz}$$

Diagram 15: Typ. Coss stored energy



$$E_{oss} = f(V_{DS})$$

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Table 20 Switching times test circuit and waveform for inductive load

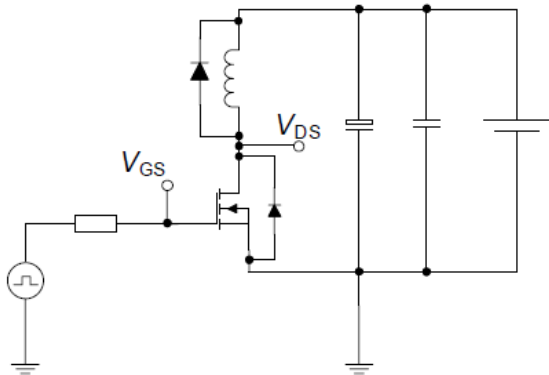
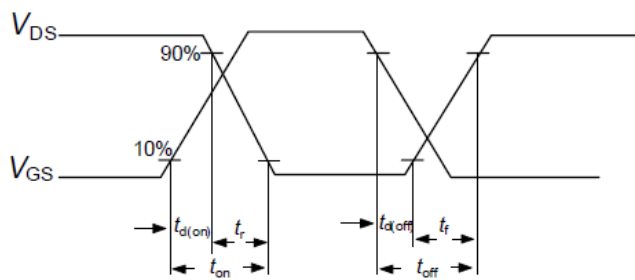
Switching times test circuit for inductive load	Switching time waveform
	

Table 21 Unclamped inductive load test circuit and waveform

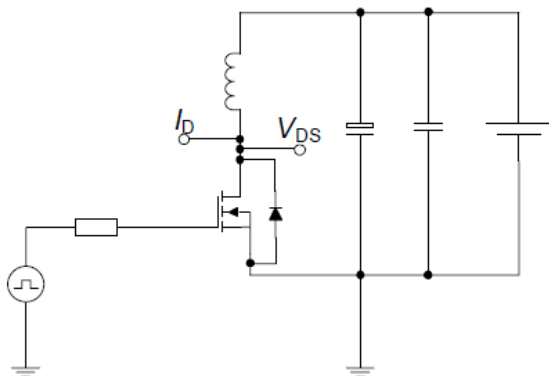
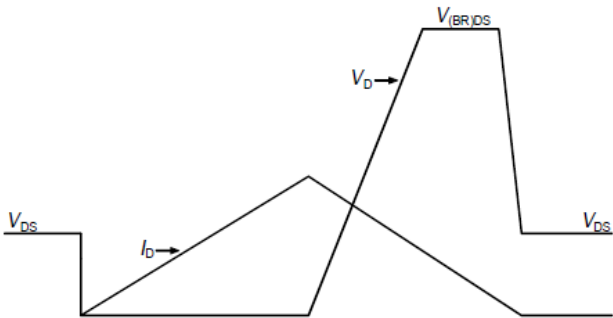
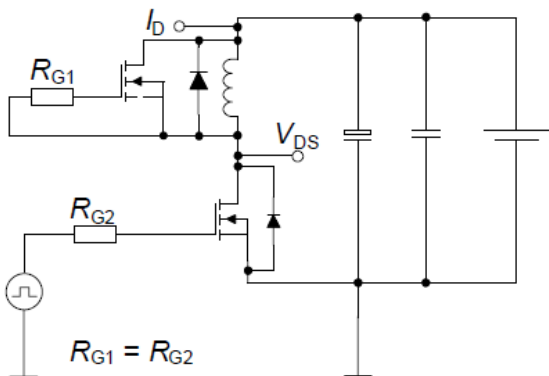
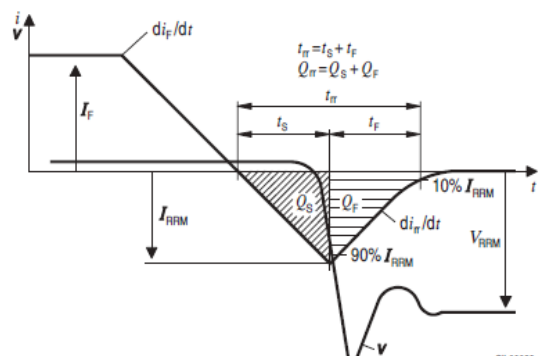
Unclamped inductive load test circuit	Unclamped inductive waveform
	

Table 22 Test circuit and waveform for diode characteristics

Test circuit for diode characteristics	Diode recovery waveform
 $R_{G1} = R_{G2}$	 SLD00088